

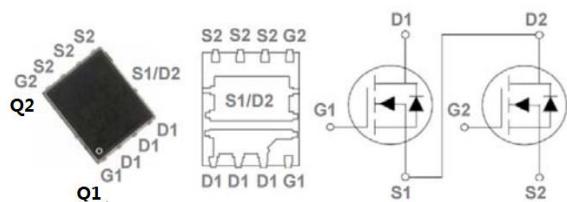
**Features**

- Dual N-Channel, Low  $R_{DS(on)}$  @  $V_{GS}=10V$
- 10V Logic Level Control
- 100% UIS Tested
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ Typ}$	$I_D \text{ Max}$
40V	3.5mΩ @ 10V	80A

**Applications**

- Load Switch
- Switching Circuits
- High Speed line Driver
- Power management

**Package**

PDFN5X6 Asym Dual

**Order Information**

Product	Package	Marking	Packing
LX56F80N40	PDFN5X6	4488	5000PCS/Reel

**Absolute Maximum Ratings**

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit
<b>Common Ratings (TA=25°C Unless Otherwise Noted)</b>			
$V_{GS}$	Gate-Source Voltage	±20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	40	V
$T_J$	Maximum Junction Temperature	150	°C
$T_{STG}$	Storage Temperature Range	-50 to 150	°C

Mounted on Large Heat Sink

$I_{DM}$	Pulse Drain Current Tested①	$T_A=25^\circ\text{C}$	220	A
$I_D$	Continuous Drain Current	$T_A=25^\circ\text{C}$	80	A
		$T_A=70^\circ\text{C}$	64	
$P_D$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	52	
EAS	Avalanche energy, single pulsed ②		110	W
$R_{euc}$	Thermal Resistance Junction-Ambient		2.4	°C/W



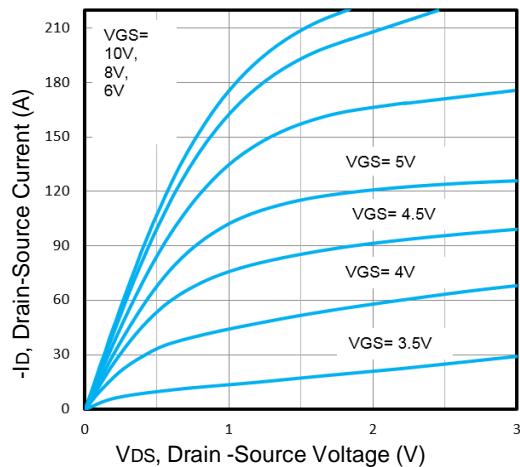
Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	40	--	--	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current( $T_A=25^\circ\text{C}$ )	$V_{DS}=40\text{V}, V_{GS}=0\text{V}$	--	--	1	$\mu\text{A}$
	Zero Gate Voltage Drain Current( $T_A=125^\circ\text{C}$ )	$V_{DS}=32\text{V}, V_{GS}=0\text{V}$	--	--	100	nA
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$	--	--	$\pm 100$	nA
$V_{GS(\text{TH})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.5	2.0	2.5	V
$R_{DS(\text{ON})}$	Drain-Source On-State Resistance②	$V_{GS}=10, I_D=15\text{A}$	--	3.5	5.0	$\text{m}\Omega$
$R_{DS(\text{ON})}$	Drain-Source On-State Resistance②	$V_{GS}=4.5\text{V}, I_D=10\text{A}$	--	7.2	9.0	$\text{m}\Omega$
<b>Dynamic Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=20\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$	--	1130	--	pF
$C_{oss}$	Output Capacitance		--	383	--	pF
$C_{rss}$	Reverse Transfer Capacitance		--	63	--	pF
$Q_g$	Total Gate Charge	$V_{DS}=20\text{V}, I_D=20\text{A}, V_{GS}=10\text{V}$	--	25	--	nC
$Q_{gs}$	Gate Source Charge		--	2.4	--	nC
$Q_{gd}$	Gate Drain Charge		--	6.9	--	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn on Delay Time	$V_{DD}=20\text{V}, I_D=1\text{A}, R_G=3.3\Omega, V_{GS}=10\text{V}$	--	8.0	--	ns
$t_r$	Turn on Rise Time		--	12	--	ns
$t_{d(off)}$	Turn Off Delay Time		-	25	--	ns
$t_f$	Turn Off Fall Time		--	18	--	ns
<b>Source Drain Diode Characteristics</b>						
$I_{SD}$	Source drain current(Body Diode)	$T_A=25^\circ\text{C}$	--	--	80	A
$V_{SD}$	Forward on voltage②	$T_J=25^\circ\text{C}, I_{SD}=5\text{A}, V_{GS}=0\text{V}$	--	0.84	1.2	V

**Notes:**

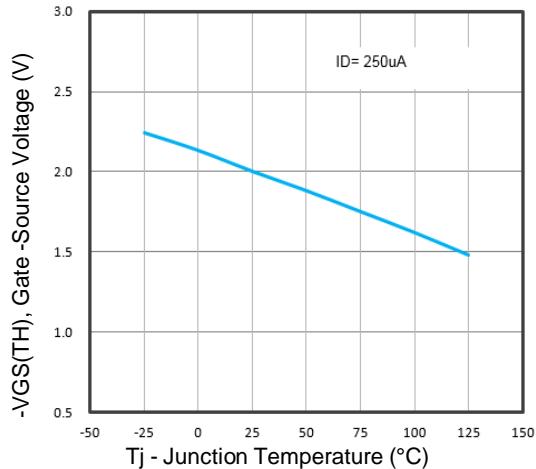
① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width $\leq 300\mu\text{s}$ , duty cycle $\leq 2\%$ .

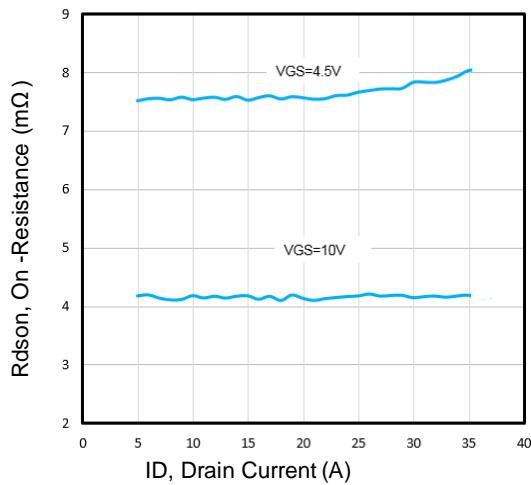
## Typical Characteristics



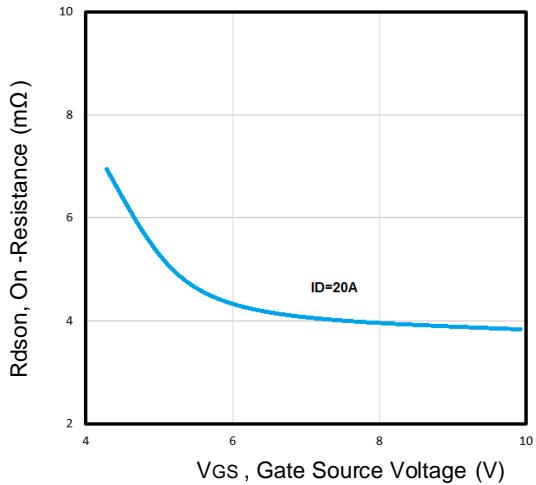
**Fig1.** Typical Output Characteristics



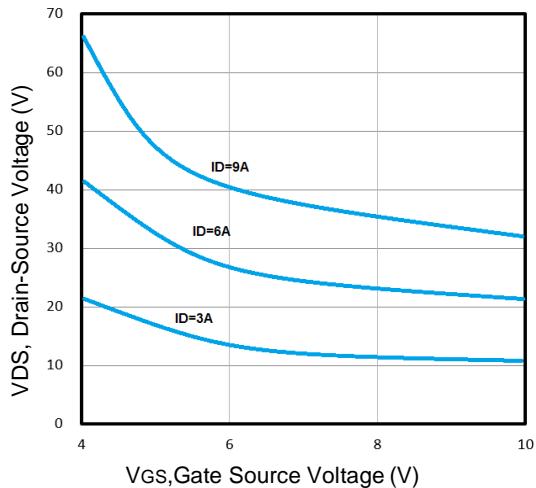
**Fig2.** Normalized Threshold Voltage Vs. Temperature



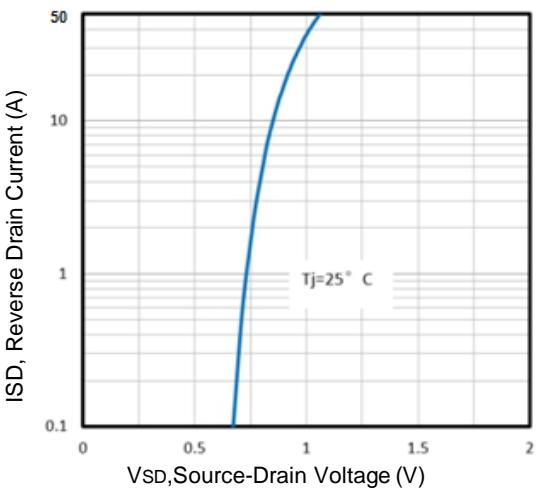
**Fig3.** On-Resistance vs. Drain Current



**Fig4.** On-Resistance vs. Gate Source Voltage



**Fig5.** Drain-Source Voltage vs Gate-Source Voltage



**Fig6.** Typical Source-Drain Diode Forward Voltage

## Typical Characteristics

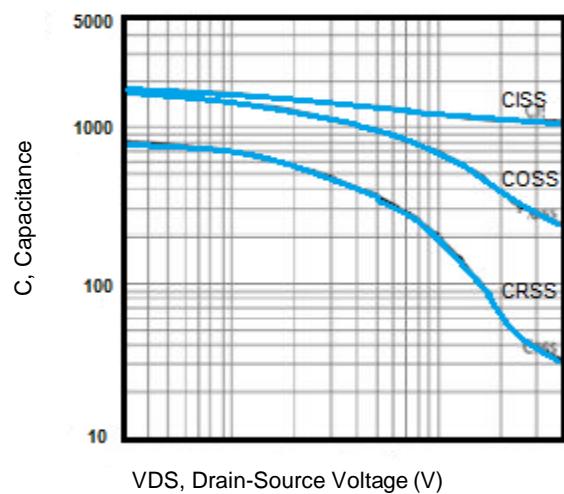


Fig7. Typical Capacitance Vs. Drain-Source Voltage

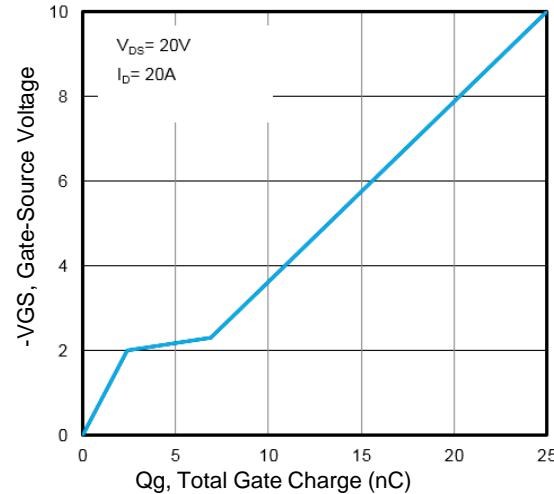


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

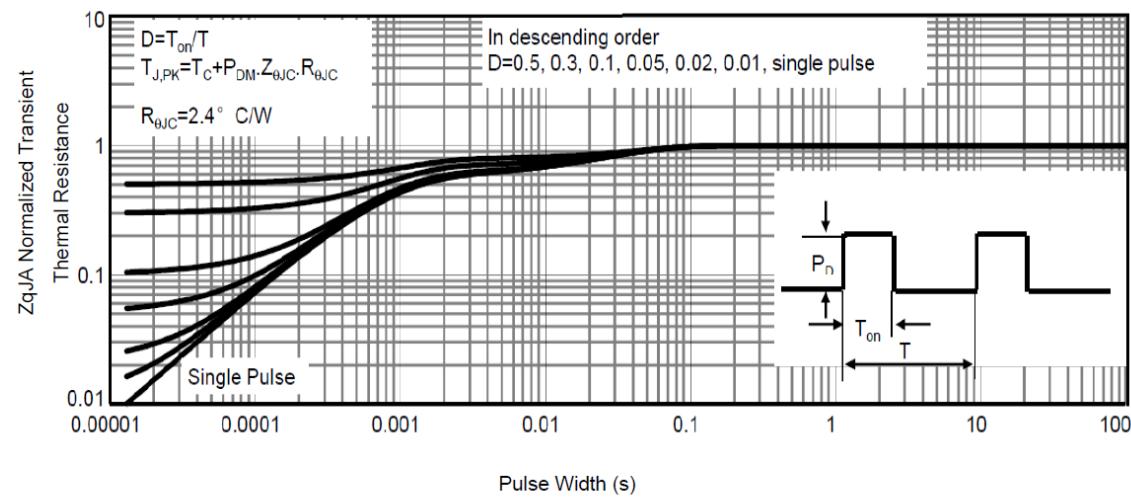


Fig9. Normalized Maximum Transient Thermal Impedance

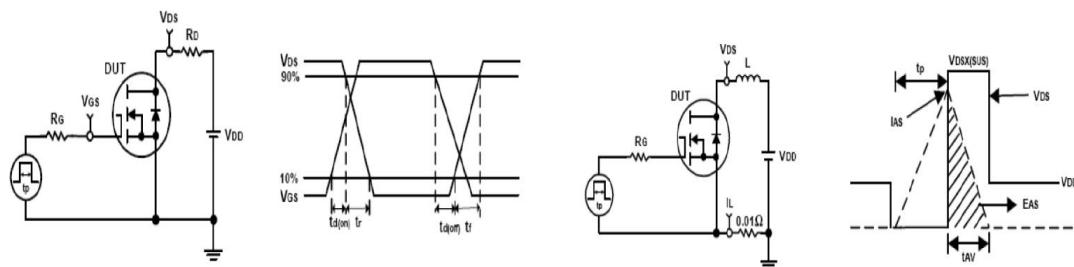


Fig10. Switching Time Test Circuit and waveforms

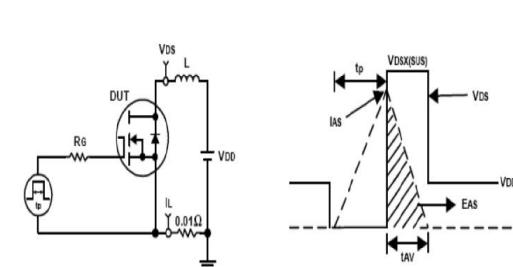
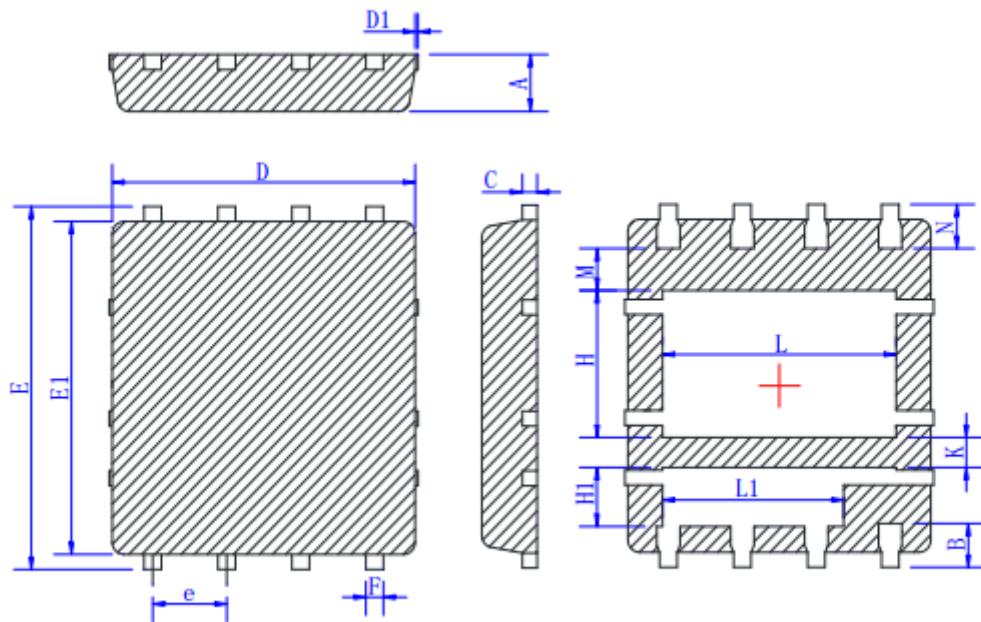


Fig11. Unclamped Inductive Test Circuit and waveforms

## PDFN5X6 Asym Dual Mechanical Data



## DIMENSIONS(unit:mm)

Symbol	Min	Typ	Max
A	0.90	0.95	1.00
B	0.60	0.70	0.80
C	0.20	0.254	0.30
D	5.10	5.20	5.30
D1			0.12
E	5.95	6.05	6.15
E1	5.40	5.55	5.70
e	1.22	1.27	1.32
F	0.25	0.30	0.35
H	2.35	2.45	2.55
H1	0.88	0.98	1.08
L	3.80	4.00	4.20
L1	3.00	3.10	3.20
M	0.60	0.70	0.80
N	0.63	0.73	0.83
K	0.40	0.50	0.60